

The 2N322, 2N323, 2N324 are alloy junction PNP transistors intended for driver service in audio amplifiers. They are miniaturized versions of the 2N190 series of G.E. transistors. By control of transistor characteristics during manufacture, a specific power gain is provided for each type. Special processing techniques and the use of hermetic seals provides stability of these characteristics throughout life.

2N322, 2N323, 2N324

Outline Drawing No. 29

SPECIFICATIONS

ABSOLUTE MAXIMUM RATINGS:

Voltages

Collector to Emitter	V _{CE}	-16 volts
Collector to Base	V _{CB}	-16 volts
Collector Current	I _C	50 ma

Power		
Collector Dissipation	P _{CM}	75 mw

Temperature	T _A -T _{STG}	-65 to +85 °C
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TYPICAL ELECTRICAL CHARACTERISTICS: (25°C)

D.C. Characteristics	2N322	2N323	2N324	
Base Current Gain (I _c = 20 ma; V _{CE} = 1v) h _{FE}	48	80	95	
Collector to Emitter Voltage (R _{EE} = 10 K, I _c = .6 ma)	V _{CE}	16	16	16 volts
Collector Cutoff Current (I _{CO})	I _{CO}	10	10	10 μ A
Max. Collector Cutoff Current (I _{CO})	I _{CO}	16	16	16 μ A

Small Signal Characteristics	2N322	2N323	2N324	
Frequency Cutoff (V _{CE} = -5v; I _c = 1 ma)	f _{ab}	29	33	34
Collector Capacity (V _{CE} = -5v; I _c = 1 ma)	C _{ab}	24	24	24 μ uf
Noise Figure (V _{CE} = -5v; I _c = 1 ma)	NF	10	10	10 db
Input Impedance (V _{CE} = -5v; I _c = 1 ma)	h _{ie}	2200	2600	3300 ohms
Current Gain (V _{CE} = -5v; I _c = 1 ma)	h _{fe}	70	84	112

Thermal Characteristics	2N322	2N323	2N324
Thermal Resistance Junction to Air	.33	.33	.33 °C/mw

Performance Data Common Emitter	2N322	2N323	2N324	
Power Gain Driver (V _{CC} = 9v)	G _e	39	41	43 db
Power Output	P _o	1	1	1 mw

